

Concl.  
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surrounding portions thereof is less likely to deteriorate, and the semiconductor laser device can increase its output power. The active layer has a quantum well structure in the illustrated embodiment but does not have to do so.

Please replace page 21, last paragraph as follows:

In addition, a Group III-V nitride semiconductor, containing gallium nitride as a main component, is used as a semiconductor material for the violet-light-emitting semiconductor laser device with an oscillation wavelength of about 400 nm. Alternatively, any of Group II-VI compound semiconductors such as zinc selenide (ZnSe), zinc sulfide (ZnS) and zinc oxide (Zno) may also be used.

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